



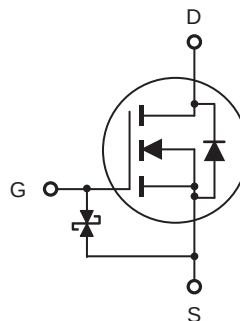
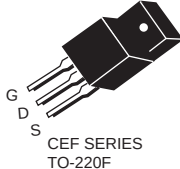
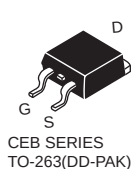
CEP01N6/CEB01N6 CEI01N6/CEF01N6

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP01N6	650V	15Ω	1A	10V
CEB01N6	650V	15Ω	1A	10V
CEI01N6	650V	15Ω	1A	10V
CEF01N6	650V	15Ω	1A ^e	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-262 package & TO-220F full-pak for through hole.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263/262	TO-220F	
Drain-Source Voltage	V _{DS}	650		V
Gate-Source Voltage	V _{GS}	±30		V
Drain Current-Continuous	I _D	1	1 ^e	A
Drain Current-Pulsed ^a	I _{DM} ^f	4	4 ^e	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P _D	36	28	W
		0.29	0.22	W/°C
Single Pulsed Avalanche Energy ^d	E _{AS}	60		mJ
Repetitive Avalanche Current	I _{AS}	0.8		A
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	3.5	4.5	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W



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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 30V, V_{DS} = 0V$			10	μA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -30V, V_{DS} = 0V$			-10	μA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.4A$		12	15	Ω
Dynamic Characteristics ^c						
Forward Transconductance	g_{FS}^b	$V_{DS} = 20V, I_D = 0.4A$		0.5		S
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$		136		pF
Output Capacitance	C_{oss}			46		pF
Reverse Transfer Capacitance	C_{rss}			19		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 0.4A,$ $V_{GS} = 10V, R_{GEN} = 4.7\Omega$		19	38	ns
Turn-On Rise Time	t_r			13	26	ns
Turn-Off Delay Time	$t_{d(off)}$			24	48	ns
Turn-On Fall Time	t_f			35	70	ns
Total Gate Charge	Q_g	$V_{DS} = 480V, I_D = 0.8A,$ $V_{GS} = 10V$		6	8	nC
Gate-Source Charge	Q_{gs}			1.0		nC
Gate-Drain Charge	Q_{gd}			4.4		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S				0.8	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 0.8A$			1.6	V
Notes :						
a.Repetitive Rating : Pulse width limited by maximum junction temperature .						
b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.						
c.Guaranteed by design, not subject to production testing.						
d.L = 190mH, $I_{AS} = 0.8A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$.						
e.Limited only by maximum temperature allowed .						
f.Pulse width limited by safe operating area .						



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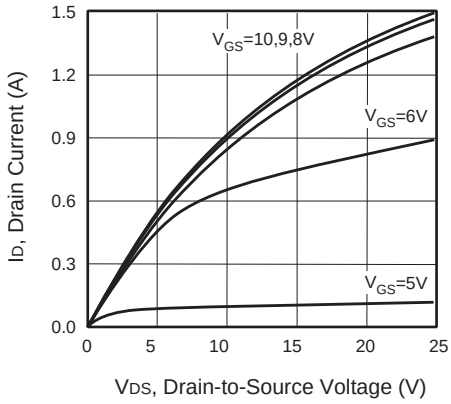


Figure 1. Output Characteristics

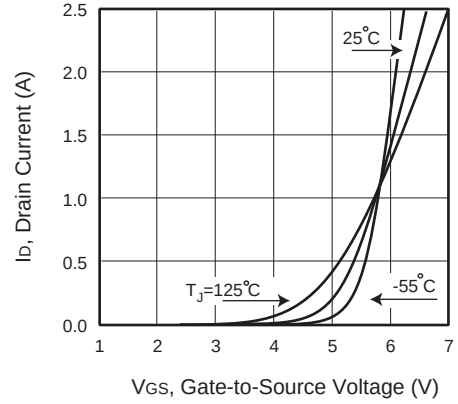


Figure 2. Transfer Characteristics

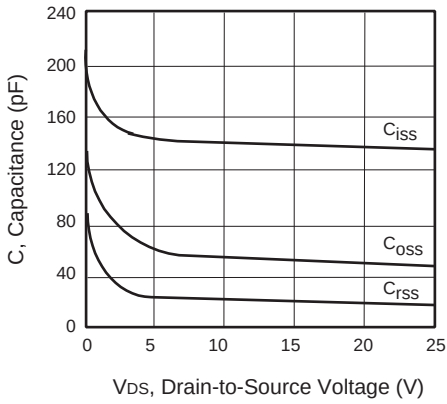


Figure 3. Capacitance

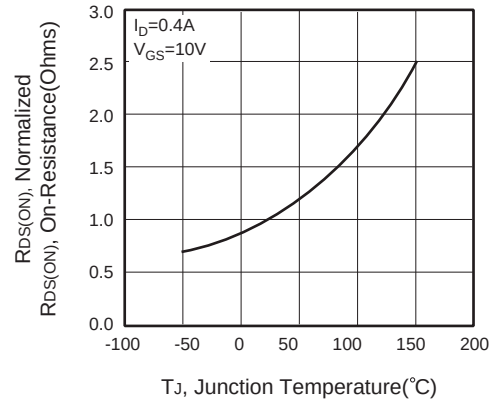


Figure 4. On-Resistance Variation with Temperature

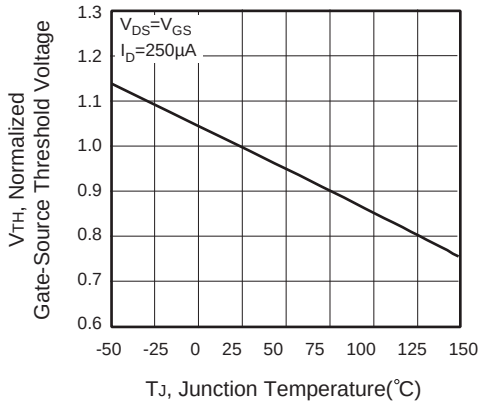


Figure 5. Gate Threshold Variation with Temperature

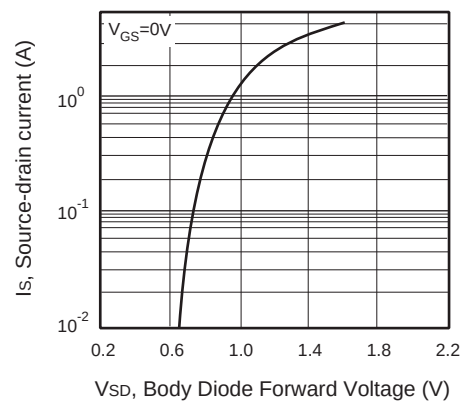


Figure 6. Body Diode Forward Voltage Variation with Source Current



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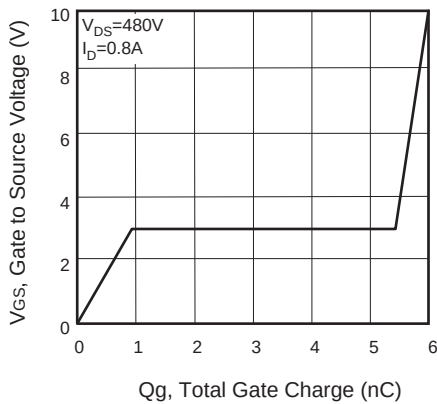


Figure 7. Gate Charge

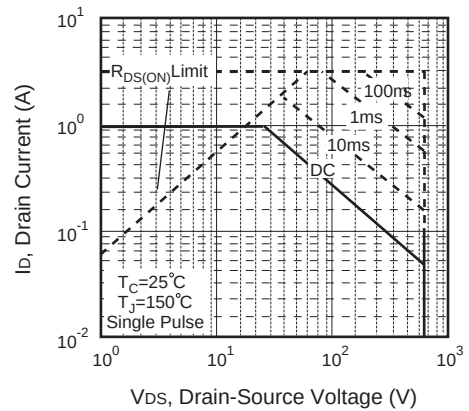


Figure 8. Maximum Safe Operating Area

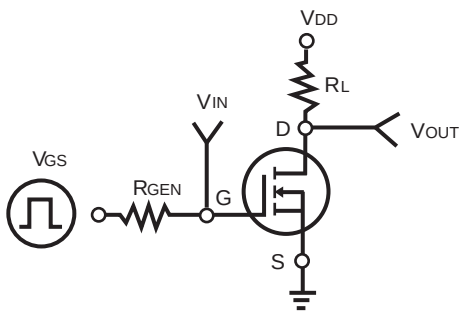


Figure 9. Switching Test Circuit

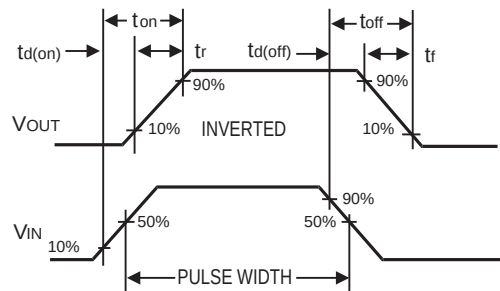


Figure 10. Switching Waveforms

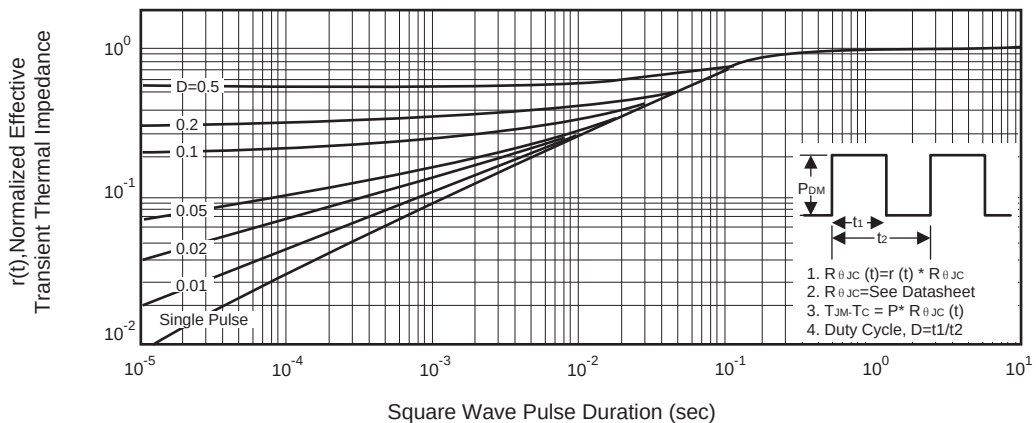


Figure 11. Normalized Thermal Transient Impedance Curve